Intelligent Power Module (IPM), 650 V, 30 A

NFAM3065L4BT

General Description

The NFAM3065L4BT is a fully-integrated inverter power module consisting of an independent High side gate driver, LVIC, six IGBT’s and a temperature sensor (VTS or Thermistor (T)), suitable for driving permanent magnet synchronous (PMSM) motors, brushless DC (BLDC) motors and AC asynchronous motors. The IGBT’s are configured in a three-phase bridge with separate emitter connections for the lower legs for maximum flexibility in the choice of control algorithm.

The power stage has undervoltage lockout protection (UVP). Internal boost diodes are provided for high side gate boost drive.

Features

- Three-phase 650 V, 30 A IGBT Module with Independent Drivers
- Active Logic Interface
- Built-in Undervoltage Protection (UVP)
- Integrated Bootstrap Diodes and Resistors
- Separate Low-side IGBT Emitter Connections for Individual Current Sensing of Each Phase
- Temperature Sensor (VTS or Thermistor (T))
- UL1557 Certified (File No.339285)
- This Device is Pb−Free and RoHS Compliant

Typical Applications

- Industrial Drives
- Industrial Pumps
- Industrial Fans
- Industrial Automation

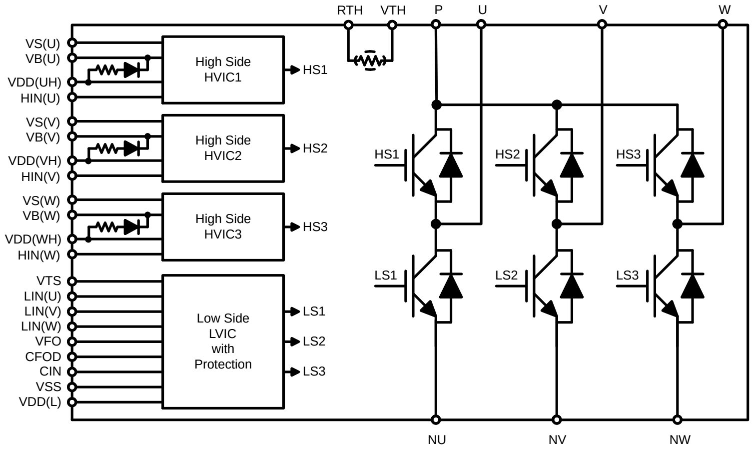

Figure 1. Application Schematic

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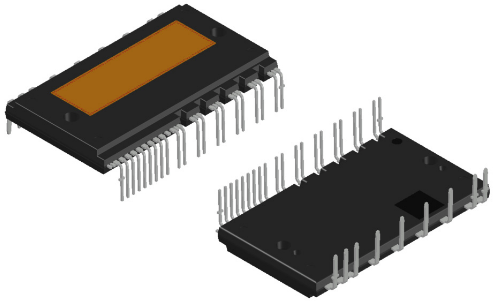


DIP39 54.5 x 31.0
CASE MODGC

MARKING DIAGRAM

Device marking is on package top side

NFAM3065L4BT = Specific Device Code
ZZZ = Assembly Lot Code
A = Assembly Location
T = Test Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NFAM3065L4BT	DIP39 54.5 x 31.0 (Pb-Free)	90 / Box

April, 2020 − Rev. 1

APPLICATION SCHEMATIC

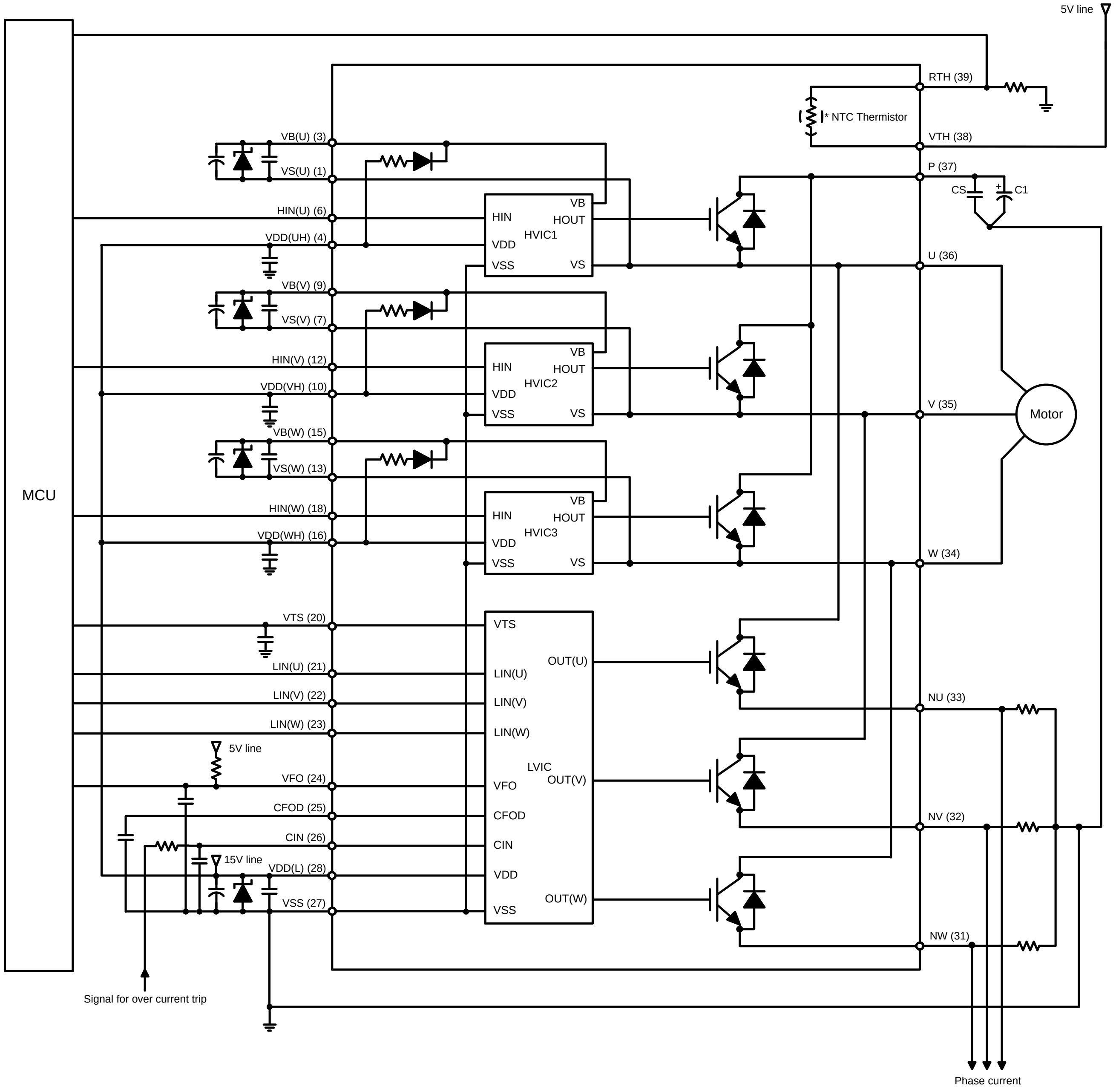


Figure 2. Application Schematic − Adjustable Option

BLOCK DIAGRAM

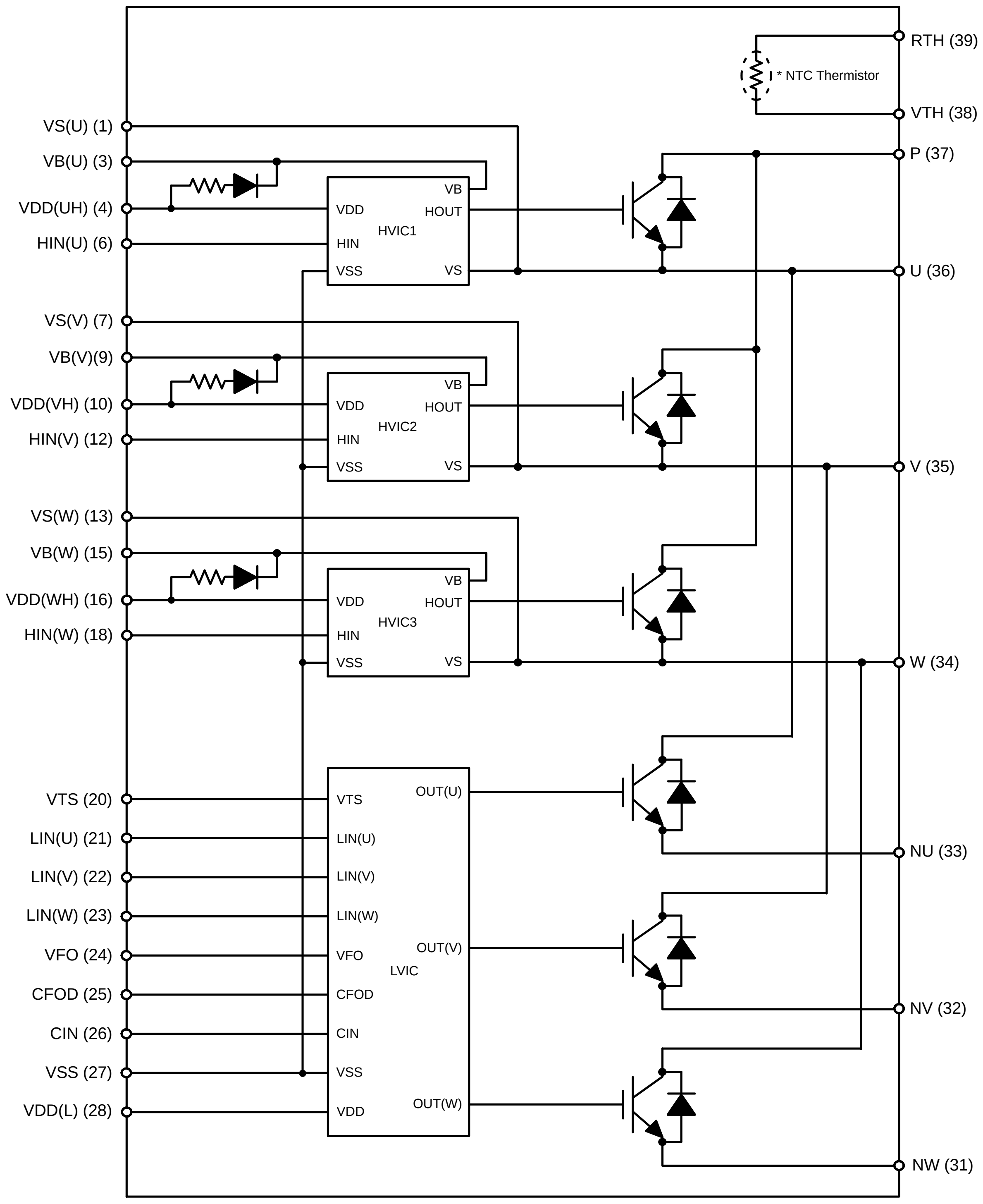


Figure 3. Equivalent Block Diagram

PIN FUNCTION DESCRIPTION

Pin	Name	Description
1	VS(U)	High-Side Bias Voltage GND for U phase IGBT Driving
(2)	−	Dummy
3	VB(U)	High-Side Bias Voltage for U phase IGBT Driving
4	VDD(UH)	High-Side Bias Voltage for U phase IC
(5)	−	Dummy
6	HIN(U)	Signal Input for High-Side U Phase
7	VS(V)	High-Side Bias Voltage GND for V phase IGBT Driving
(8)	−	Dummy
9	VB(V)	High-Side Bias Voltage for V phase IGBT Driving
10	VDD(VH)	High-Side Bias Voltage for V phase IC
(11)	−	Dummy
12	HIN(V)	Signal Input for High-Side V Phase
13	VS(W)	High-Side Bias Voltage GND for W phase IGBT Driving
(14)	−	Dummy
15	VB(W)	High-Side Bias Voltage for W phase IGBT Driving
16	VDD(WH)	High-Side Bias Voltage for W phase IC
(17)	−	Dummy
18	HIN(W)	Signal Input for High-Side W Phase
(19)	−	Dummy
20	VTS	Voltage Output for LVIC Temperature Sensing Unit
21	LIN(U)	Signal Input for Low-Side U Phase
22	LIN(V)	Signal Input for Low-Side V Phase
23	LIN(W)	Signal Input for Low-Side W Phase
24	VFO	Fault Output
25	CFOD	Capacitor for Fault Output Duration Selection
26	CIN	Input for Current Protection
27	VSS	Low-Side Common Supply Ground
28	VDD(L)	Low-Side Bias Voltage for IC and IGBTs Driving
(29)	−	Dummy
(30)	−	Dummy
31	NW	Negative DC-Link Input for U Phase
32	NV	Negative DC-Link Input for V Phase
33	NU	Negative DC-Link Input for W Phase
34	W	Output for U Phase
35	V	Output for V Phase
36	U	Output for W Phase
37	P	Positive DC-Link Input
38	VTH	Thermistor Bias Voltage (T) / Not connection
39	RTH	Series Resister for Thermistor (Temperature Detection) *optional for T

1. Pins of () are the dummy for internal connection. These pins should be no connection.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C) (Note 2)

Symbol	Rating	Conditions	Value	Unit
VPN	Supply Voltage	P−NU, NV, NW	450	V
VPN(surge)	Supply Voltage (Surge)	P−NU, NV, NW (Note 3)	550	V
VPN(PROT)	Self Protection Supply Voltage Limit (Short-Circuit Protection Capability)	VDD = VBS = 13.5 V to 16.5 V, Tj = 150°C, VCES < 650 V, Non-Repetitive, < 2 μs	400	V
Vces	Collector-emitter Voltage		650	V
VRRM	Maximum Repetitive Revers Voltage		650	V
±Ic	Each IGBT Collector Current		±30	A
±Icp	Each IGBT Collector Current (Peak)	Under 1ms Pulse Width	±60	A
VDD	Control Supply Voltage	VDD(UH,VH,WH), VDD(L)−VSS	−0.3 to 20	V
VBS	High-Side Control Bias voltage	VB(U)−VS(U), VB(V)−VS(V), VB(W)−VS(W)	−0.3 to 20	V
VIN	Input Signal Voltage	HIN(U), HIN(V), HIN(W), LIN(U), LIN(V), LIN(W)–VSS	−0.3 to VDD	V
VFO	Fault Output Supply Voltage	VFO–VSS	−0.3 to VDD	V
IFO	Fault Output Current	Sink Current at VFO pin	2	mA
VCIN	Current Sensing Input Voltage	CIN–VSS	−0.3 to VDD	V
Pc	Corrector Dissipation	Per One Chip	113	W
Tj	Operating Junction Temperature		−40 to +150	°C
Tstg	Storage Temperature		−40 to +125	°C
Tc	Module Case Operation Temperature		−40 to +125	°C
Viso	Isolation Voltage	60 Hz, Sinusoidal, AC 1 minute, Connection Pins to Heat Sink Plate	2500	V rms

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.
3. This surge voltage developed by the switching operation due to the wiring inductance between P and NU, NV, NW terminal.

THERMAL CHARACTERISTICS

Symbol	Rating	Conditions	Min	Typ	Max	Unit
$R_{th(j-c)Q}$	Junction-to-Case Thermal Resistance	Inverter IGBT Part (per 1/6 module)	−	−	1.1	°C/W
$R_{th(j-c)F}$		Inverter FWD Part (per 1/6 module)	−	−	2.2	°C/W

4. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

RECOMMENDED OPERATING CONDITIONS

Symbol	Rating	Conditions		Min	Typ	Max	Unit
VPN	Supply Voltage	P−NU, NV, NW		−	300	400	V
VDD	Gate Driver Supply Voltages	VDD(UH,VH,WH), VDD(L)−VSS		13.5	15	16.5	V
VBS		VB(U)−VS(U), VB(V)−VS(V), VB(W)−VS(W)		13.0	15	18.5	V
dVDD / dt, dVBS / dt	Supply Voltage Variation			−1	−	1	V/µs
fPWM	PWM Frequency			1	−	20	kHz
DT	Dead Time	Turn-off to Turn-on (external)		1.5	−	−	µs
Io	Allowable r.m.s. Current	VPN = 300 V, VDD = 15 V, P.F. = 0.8 Tc ≤ 125°C, Tj ≤ 150°C (Note 5)	f_{PWM} = 5 kHz	−	−	25.7	A rms
			f_{PWM} = 15 kHz	−	−	18.8	
PWIN (on)	Allowable Input Pulse Width	200 V ≤ VPN ≤ 400 V 13.5 V ≤ VDD ≤ 16.5 V 13.0 V ≤ VBS ≤ 18.5 V −20°C ≤ Tc ≤ 100°C		1.0	−	−	µs
PWIN (off)				1.5	−	−	
	Package Mounting Torque	M3 type screw		0.6	0.7	0.9	Nm

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Allowable r.m.s current depends on the actual conditions.
6. Flatness tolerance of the heatsink should be within −50 µm to +100 µm.

ELECTRICAL CHARACTERISTICS (T_C = 25°C, VDD = 15 V, VBS = 15 V, unless otherwise specified.) (Note 7)

INVERTER SECTION

Symbol	Parameter		Test Conditions	Min	Typ	Max	Unit
Ices	Collector-Emitter Leakage Current		Vce = Vces, Tj = 25°C	−	−	1	mA
			Vce = Vces, Tj = 150°C	−	−	10	mA
VCE(sat)	Collector-Emitter Saturation Voltage		VDD = VBS = 15 V, IN = 5 V Ic = 30 A, Tj = 25°C	−	1.60	2.30	V
			VDD = VBS = 15 V, IN = 5 V Ic = 30 A, Tj = 150°C	−	1.80	−	V
VF	FWDi Forward Voltage		IN = 0 V, Ic = 30 A, Tj = 25°C	−	2.00	2.40	V
			IN = 0 V, Ic = 30 A, Tj = 150°C	−	2.00	−	V
ton	Switching Times	High Side	VPN = 300 V, VDD(H) = VDD(L) = 15 V Ic = 30 A, Tj = 25°C, IN = 0 ⇔ 5 V Inductive Load	0.80	1.25	1.85	µs
tc(on)				−	0.25	0.65	µs
toff				−	1.60	2.20	µs
tc(off)				−	0.25	0.75	µs
trr				−	0.15	−	µs
ton		Low Side	VPN = 300 V, VDD(H) = VDD(L) = 15 V Ic = 30 A, Tj = 25°C, IN = 0 ⇔ 5 V Inductive Load	0.80	1.40	2.00	µs
tc(on)				−	0.25	0.55	µs
toff				−	1.60	2.20	µs
tc(off)				−	0.25	0.75	µs
trr				−	0.10	−	µs

ELECTRICAL CHARACTERISTICS (T_C = 25°C, VDD = 15 V, VBS = 15 V, unless otherwise specified.) (Note 7) (continued)

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit

DRIVER SECTION

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
IQDDH	Quiescent VDD Supply Current	VDD(UH,VH,WH) = 15 V, HIN(U,V,W) = 0 V	VDD(UH)−VSS VDD(VH)−VSS VDD(WH)−VSS	−	−	0.30	mA
IQDDL		VDD(L) = 15 V, LIN(U,V,W) = 0 V	VDD(L)−VSS	−	−	3.50	mA
IPDDH	Operating VCC Supply Current	VDD(UH,VH,WH) = 15 V, f_{PWM} = 20 kHz, Duty = 50%, Applied to one PWM Signal Input for High-Side	VDD(UH)−VSS VDD(VH)−VSS VDD(WH)−VSS	−	−	0.40	mA
IPDDL		VDD(L) = 15 V, f_{PWM} = 20 kHz, Duty = 50%, Applied to one PWM Signal Input for Low-Side	VDD(L)−VSS	−	−	6.00	mA
IQBS	Quiescent VBS Supply Current	VBS = 15 V, HIN(U,V,W) = 0 V	VB(U)−VS(U) VB(V)−VS(V) VB(W)−VS(W)	−	−	0.30	mA
IPBS	Operating VBS Supply Current	VDD = VBS = 15 V, f_{PWM} = 20 kHz, Duty = 50%, Applied to one PWM Signal Input for High-Side	VB(U)−VS(U) VB(V)−VS(V) VB(W)−VS(W)	−	−	5.00	mA
VIN(ON)	ON Threshold Voltage	HIN(U,V,W)−VSS, LIN(U,V,W)−VSS		−	−	2.6	V
VIN(OFF)	OFF Threshold Voltage			0.8	−	−	V
VCS(ref)	Short Circuit Trip Level	VDD = 15 V, CIN−VSS		0.46	0.48	0.50	V
UVDDD	Supply Circuit Under-Voltage Protection	Detection Level		10.3	−	12.5	V
UVDDR		Reset Level		10.8	−	13.0	V
UVBSD		Detection Level		10.0	−	12.0	V
UVBSR		Reset Level		10.5	−	12.5	V
VTS	Voltage Output for LVIC Temperature Sensing Unit	VTS−VSS = 10 nF, Temp. = 25°C		0.905	1.030	1.155	V
VFOH	Fault Output Voltage	VDD = 0 V, CIN = 0 V, VFO Circuit: 10 kΩ to 5 V Pull-up		4.9	−	−	V
VFOL		VDD = 0 V, CIN = 1 V, VFO Circuit: 10 kΩ to 5 V Pull-up		−	−	0.95	V
t_{FOD}	Fault-Output Pulse Width	CFOD = 22 nF		1.6	2.4	−	ms

BOOTSTRAP SECTION

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
VF	Bootstrap Diode Forward Voltage	If = 0.1 A		3.4	4.6	5.8	V
RBOOT	Built-in Limiting Resistance			30	38	46	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Performance guaranteed over the indicated operating temperature range by design and/or characterization tested at $T_J = T_A$ = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
8. The fault-out pulse width t_{FOD} depends on the capacitance value of CFOD according to the following approximate equation: $t_{FOD} = 0.1 \times 10^6 \times \text{CFOD (s)}$.
9. Values based on design and/or characterization.

Temperature of LVIC versus VTS Characteristics

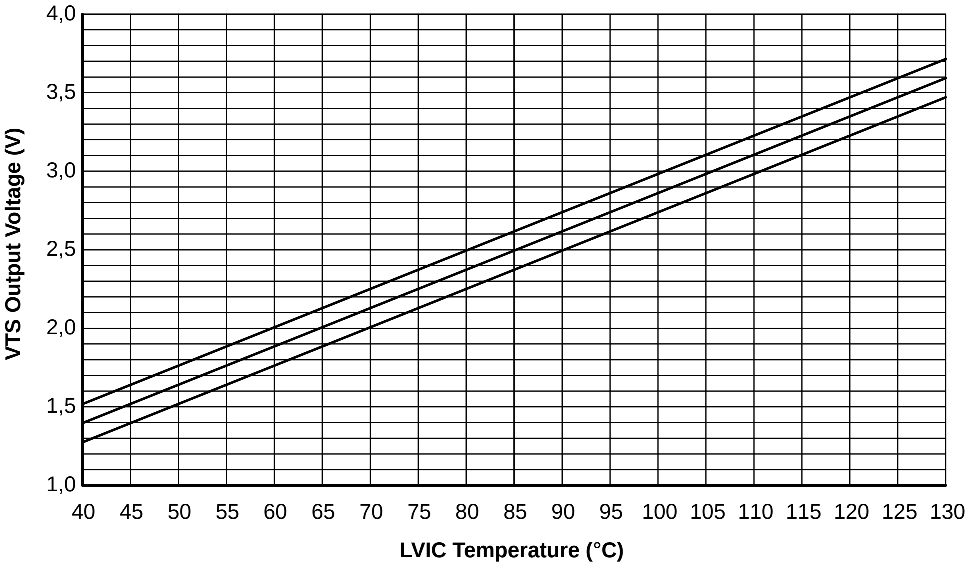


Figure 4. Temperature of LVIC versus VTS Characteristics

Table 1. THERMISTOR CHARACTERISTICS (INCLUDED ONLY IN NFAM3060L4BT)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Resistance	R_{25}	Tc = 25°C	46.530	47	47.47	kΩ
Resistance	R_{125}	Tc = 100°C	1.344	1.406	1.471	kΩ
B-Constant (25−50°C)	−	B	4009.5	4050	4090.5	K
Temperature range	−	−	−40	−	+125	°C

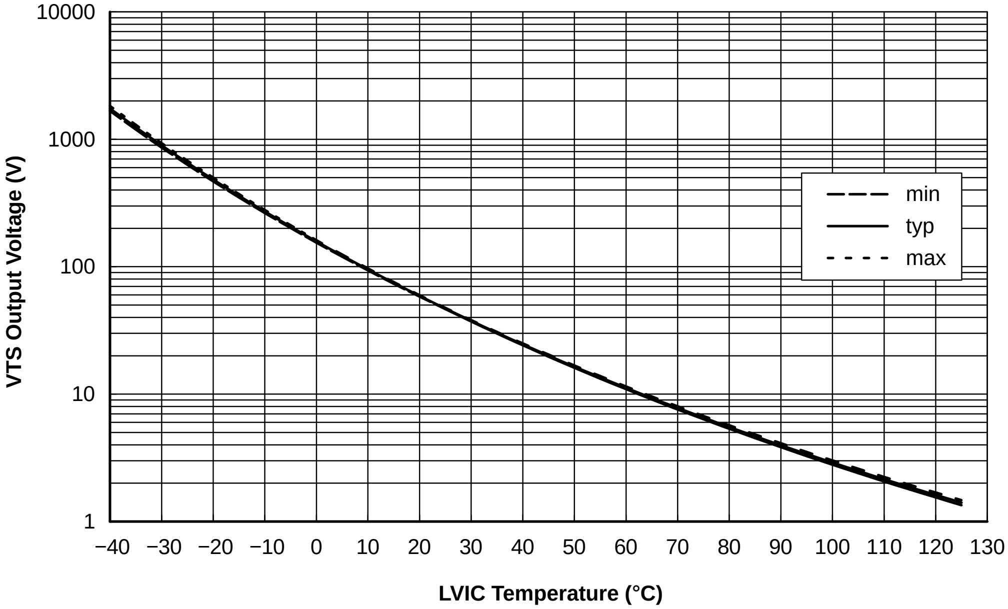
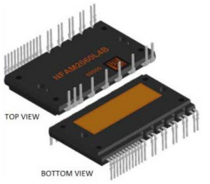


Figure 5. Thermistor Resistance versus Case Temperature



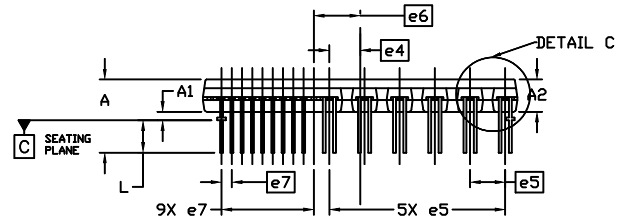
MINI DIP39, 31.0x54.5
CASE MODGC
ISSUE A

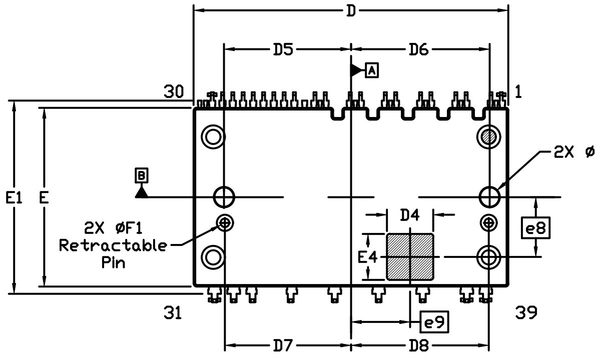
DATE 19 MAR 2019

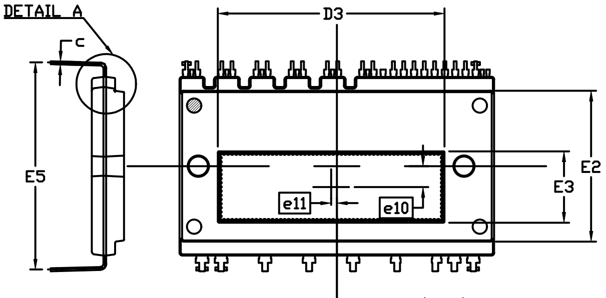
NOTES:
1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b and c APPLY TO THE PLATED LEADS AND ARE MEASURED BETWEEN 1.00 AND 2.00 FROM THE LEAD TIP.
4. POSITION OF THE LEAD IS DETERMINED AT THE ROOT OF THE LEAD WHERE IT EXITS THE PACKAGE BODY.
5. SHORTENED/CUT PINS ARE 2,5,8,11,14,17,19,29 AND 30.

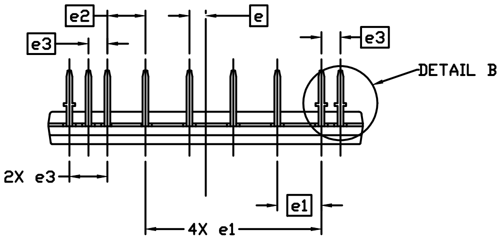
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	12.20	12.7	13.2
A1	1.00	1.50	2.00
A2	5.50	5.60	5.70
A3	2.00 REF		
A4	1.55 REF		
A5	3.10 REF		
b	0.90	1.00	1.10
b1	1.90	2.00	2.10
b2	0.40	0.50	0.60
b3	1.40	1.50	1.60
c	0.50 REF		
D	54.40	54.50	54.60
D3	39.25 REF		
D4	8.00 REF		
D5	22.00 REF		
D6	24.00 REF		
D7	21.85 REF		
D8	23.85 REF		

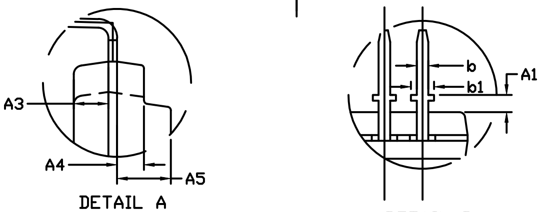
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E	30.90	31.00	31.10
E1	33.50 REF		
E2	26.14 REF		
E3	12.35 REF		
E4	8.00 REF		
E5	35.40	35.90	36.40
e	2.81 REF		
e1	7.62 BSC		
e2	6.60 BSC		
e3	3.30 BSC		
e4	5.35 REF		
e5	6.10 BSC		
e6	8.02 REF		
e7	1.78 BSC		
e8	10.35 REF		
e9	10.25 REF		
e10	3.60 REF		
e11	1.00 REF		
e12	0.89 BSC		
F	3.20	3.30	3.40
F1	1.40	1.50	1.60
L	5.60 REF		

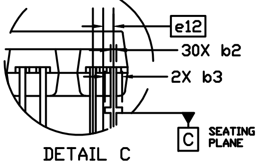












GENERIC MARKING DIAGRAM*

XXXXXXXXXXXXXXXXXX
ZZZATYWW
○

XXXXX = Specific Device Code
ZZZ = Assembly Lot Code
AT = Assembly & Test Location
Y = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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